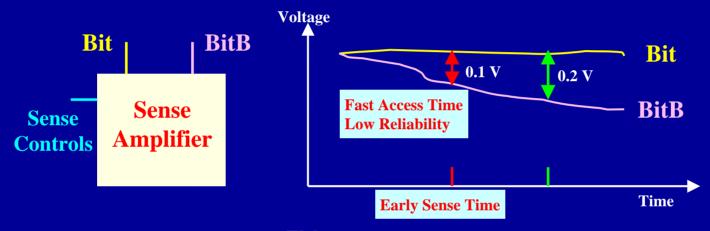
Read Margin Check

Sense-Amp Signal vs Internal Noise



- CharFlo-Memory!TM can locate
 - Bit and BitB signal
 - Sense control signal

Any change on voltage supply, .temp, process corners will impact Bit, BitB and Sense Controls.

• CharFlo-Memory!TM can automate the simulation output and measurement for reliability check



Determine Read-Margin Setting

Checking for Yields and Speed

Determine Read-Margin setting based upon access time,
Voltage(Bit-BitB) against noise-margin

Read Margin	Access Time	V(Bit-BitB)	SRAM 8Kx24
1000	4.3212 ns	365.8 mv	Slow
0100	1.8824 ns	95.9 mv	
1101	2.8109 ns	200.6 mv	
0111	1.8824 ns	95.9 mv	
1111	1.6969 ns	68.3 mv	Danger

^{*} Noise margin is 100 mv minimum normally, and 200 mv for the safer.

Wrong Read Margin (RM) setting causes Poor Yield!

